Datasheet

ROHM

Pch -20V -100mA Small Signal MOSFET

V_{DSS}	-20V
R _{DS(on)} (Max.)	3.8Ω
I _D	-100mA
P_D	150mW

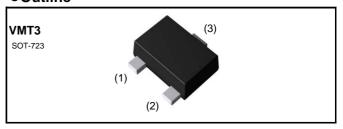
● Features

- Low voltage drive(1.2V) makes this device ideal for partable equipment.
- 2) Drive circuits can be simple.
- 3) Built-in G-S Protection Diode.

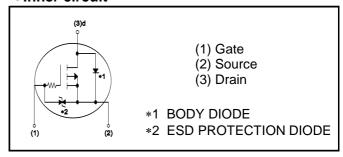
Application

Switching

Outline



•Inner circuit



Packaging specifications

	Packaging	Taping
	Reel size (mm)	180
Type	Tape width (mm)	5.5
Type	Basic ordering unit (pcs)	8,000
	Taping code	T2L
	Marking	RX

● Absolute maximum ratings(T_a = 25°C)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	-20	V
Continuous drain current	I _D *1	±100	mA
Pulsed drain current	I _{D,pulse} *2	±400	mA
Gate - Source voltage	V_{GSS}	±10	V
Power dissipation	P _D *3	150	mW
Junction temperature	T _j	150	°C
Range of storage temperature	T _{stg}	-55 to +150	°C

●Thermal resistance

Parameter	Symbol	Values			Lloit
Farameter	Symbol	Min.	Тур.	Max.	Unit
Thermal resistance, junction - ambient	R _{thJA} *3	-	-	833	°C/W

•Electrical characteristics($T_a = 25$ °C)

Darameter	Symbol	Conditions	Values			Unit
Parameter	Symbol Conditions –		Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$, $I_D = -1mA$	-20	-	-	V
Zero gate voltage drain current	I _{DSS}	$V_{DS} = -20V, V_{GS} = 0V$	ı	-	-1	μΑ
Gate - Source leakage current	I _{GSS}	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	ı	ı	±10	μΑ
Gate threshold voltage	V _{GS (th)}	$V_{DS} = -10V, I_{D} = -100uA$	-0.3	ı	-1.0	V
	R _{DS(on)} *4	$V_{GS} = -4.5V, I_D = -100 \text{mA}$	ı	2.5	3.8	
		$V_{GS} = -2.5V, I_{D} = -50 \text{mA}$	ı	3.4	5.1	
Static drain - source		$V_{GS} = -1.8V, I_{D} = -20 \text{mA}$	-	4.8	8.2	0
on - state resistance		$V_{GS} = -1.5V, I_{D} = -10mA$	-	6.0	13.2	Ω
		$V_{GS} = -1.2V, I_{D} = -1mA$	-	10.0	40.0	
		$V_{GS} = -4.5V$, $I_D = -100$ mA, $T_j = 125$ °C	-	4.8	6.8	
Transconductance	g _{fs} *4	$V_{DS} = -10V, I_{D} = -100 \text{mA}$	120	-	-	mS

^{*1} Limited only by maximum temperature allowed.

^{*2} Pw \leq 10 μ s, Duty cycle \leq 1%

^{*3} Each therminal mounted on a recommended land

^{*4} Pulsed

• Electrical characteristics ($T_a = 25$ °C)

Parameter	Symbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	15	-	
Output capacitance	C _{oss}	$V_{DS} = -10V$	-	4.0	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	1.5	-	
Turn - on delay time	t _{d(on)} *4	$V_{DD} \simeq -10V, \ V_{GS} = -4.5V$	-	46	-	
Rise time	t _r *4	$I_D = -50 \text{mA}$	-	62	-	no
Turn - off delay time	t _{d(off)} *4	$R_L = 200\Omega$	-	325	-	ns
Fall time	t _f *4	$R_G = 10\Omega$	ı	137	-	

•Body diode electrical characteristics (Source-Drain)($T_a = 25$ °C)

Parameter	Symbol	Conditions	Values			Unit
r arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Continuous source current	I _S *1	T _c = 25°C	-	-	-100	mA
Pulsed source current	I _{SM} *2	1 _c = 25 C	-	-	-400	mA
Forward voltage	V _{SD} *4	$V_{GS} = 0V, I_{s} = -100 \text{mA}$	-	-	-1.2	V

Fig.1 Power Dissipation Derating Curve

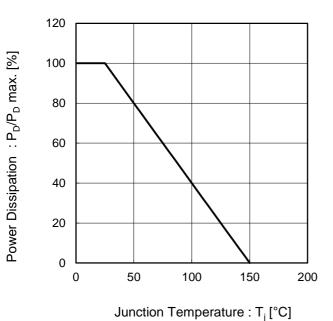


Fig.2 Drain Current Derating Curve

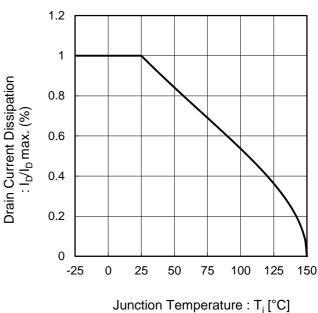


Fig.3 Typical Output Characteristics(I)

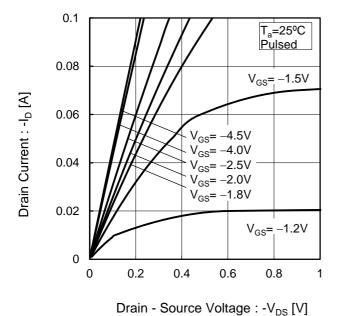
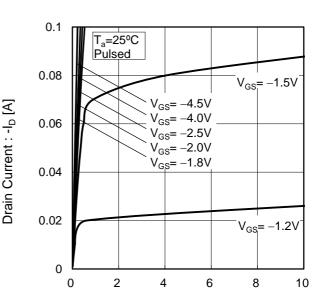


Fig.4 Typical Output Characteristics(II)



Drain - Source Voltage : -V_{DS} [V]

Drain - Source Breakdown Voltage : -V_{(BR)DSS}

Gate Threshold Voltage: -VGS(th) [V]

•Electrical characteristic curves

Fig.5 Breakdown Voltage

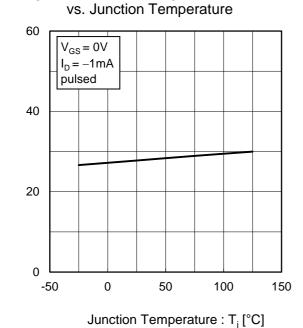
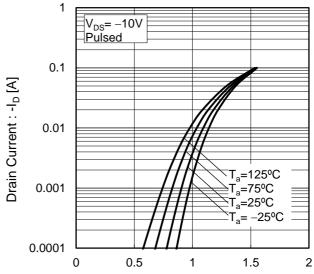


Fig.6 Typical Transfer Characteristics



Gate - Source Voltage : -V_{GS} [V]

Fig.7 Gate Threshold Voltage vs. Junction Temperature

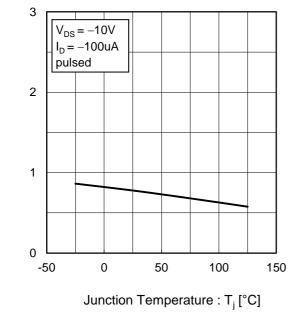
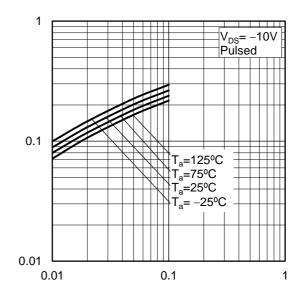
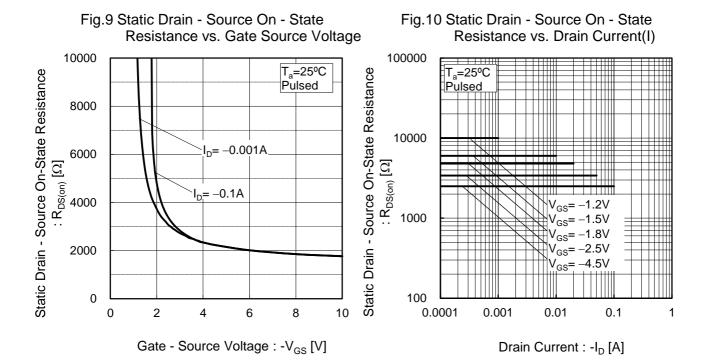


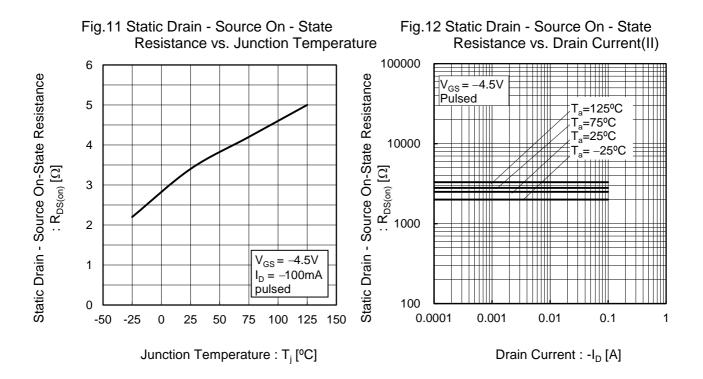
Fig.8 Transconductance vs. Drain Current



Drain Current : -I_D [A]

Transconductance: gfs [S]

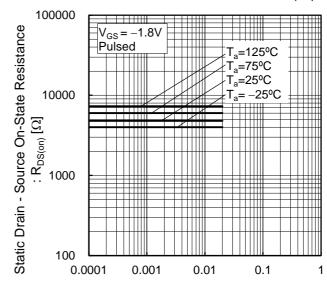




Resistance vs. Drain Current(III) 100000 $V_{GS} = -2.5V$ Static Drain - Source On-State Resistance Pulsed 10000 $:R_{\mathsf{DS}(\mathsf{on})}\left[\Omega \right]$ _=75°C 1000 =25°C -25°C 100 0.0001 0.001 0.01 0.1

Fig.13 Static Drain-Source On-State

Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(IV)



Drain Current : -I_D [A]

Fig.15 Static Drain - Source On - State

Resistance vs. Drain Current(V)

100000

V_{GS} = -1.5V

Pulsed

T_a = 125°C

T_a = 25°C

T_a = -25°C

T_a = -25°C

O 0.0001

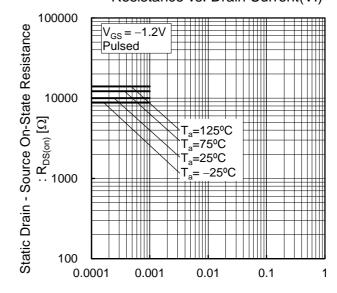
0.001

0.01

1

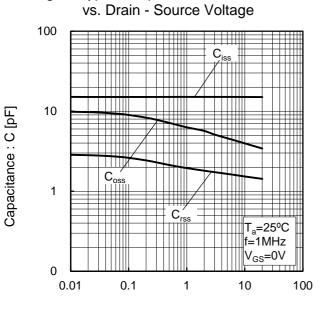
Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(VI)

Drain Current: -ID [A]



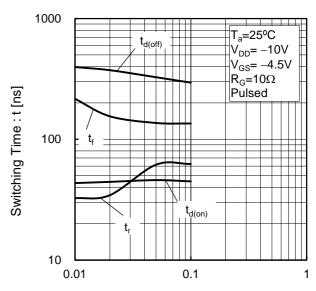
Drain Current : $-I_D$ [A] Drain Current : $-I_D$ [A]

Fig.17 Typical Capacitance



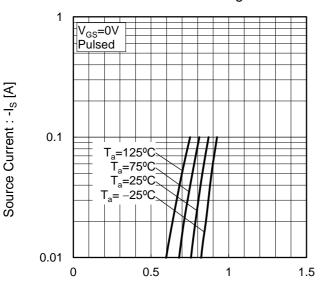
Drain - Source Voltage : -V_{DS} [V]

Fig.18 Switching Characteristics



Drain Current : -I_D [A]

Fig.19 Source Current vs. Source Drain Voltage



Source-Drain Voltage: -V_{SD}[V]

●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

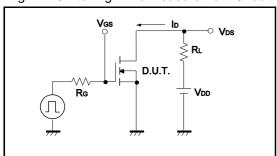
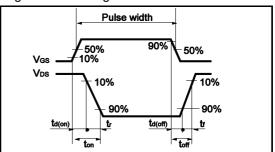


Fig.1-2 Switching Waveforms



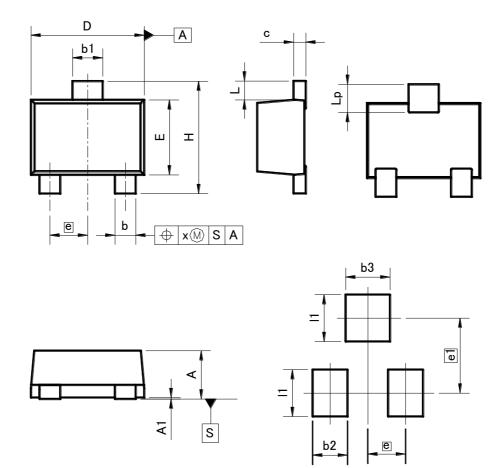
●Notice

This product might cause chip aging and breakdown under the large electrified environment.

Please consider to design ESD protection circuit.

●Dimensions (Unit:mm)

VMT3



Patterm of terminal position areas

DIM	MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	0.45	0.55	0.018	0.022
A1	0.00	0.10	0	0.004
b	0.17	0.27	0.007	0.011
b1	0.27	0.37	0.011	0.015
С	0.08	0.18	0.003	0.007
D	1.10	1.30	0.043	0.051
E	0.70	0.90	0.028	0.035
е	0.4	40	0.0	02
HE	1.10	1.30	0.043	0.051
L	0.10	0.30	0.004	I
Lp	0.20	0.40	0.008	
х	_	0.10		0.004

DIM	MILIMETERS		INCHES		
I DIM -	MIN	MAX	MIN	MAX	
e1	0.8	80	0.03		
b2	=	0.37	ı	0.015	
b3	-	0.47		0.019	
11	_	0.50		0.02	

Dimension in mm/inches

Notes

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